

CoolMOS™ Power Transistor
Features

- New revolutionary high voltage technology
- Extreme dv/dt rated
- High peak current capability
- Qualified according to JEDEC¹⁾ for target applications
- Pb-free lead plating; RoHS compliant
- Ultra low gate charge
- Ultra low effective capacitances
- Fully isolated package (2500 VAC; 1 minute)

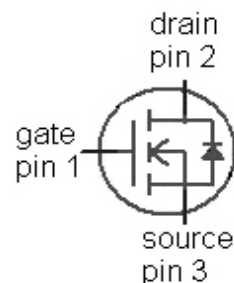
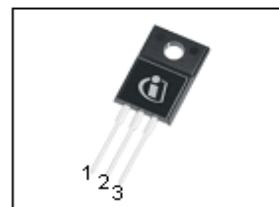
CoolMOS™ 800V designed for:

- Industrial application with high DC bulk voltage
- Switching Application (i.e. active clamp forward)

Product Summary

| | | |
|--|------|----------|
| V_{DS} | 800 | V |
| $R_{DS(on)max}$ @ $T_j = 25^\circ\text{C}$ | 0.65 | Ω |
| $Q_{g,typ}$ | 45 | nC |

PG-TO220FP



| Type | Package | Marking |
|------------|------------|---------|
| SPA08N80C3 | PG-TO220FP | 08N80C3 |

Maximum ratings, at $T_j=25^\circ\text{C}$, unless otherwise specified

| Parameter | Symbol | Conditions | Value | Unit |
|---|----------------|--|-------------|------------------|
| Continuous drain current ²⁾ | I_D | $T_C=25^\circ\text{C}$ | 8 | A |
| | | $T_C=100^\circ\text{C}$ | 5.1 | |
| Pulsed drain current ³⁾ | $I_{D,pulse}$ | $T_C=25^\circ\text{C}$ | 24 | |
| Avalanche energy, single pulse | E_{AS} | $I_D=1.6\text{ A}, V_{DD}=50\text{ V}$ | 340 | mJ |
| Avalanche energy, repetitive t_{AR} ^{3),4)} | E_{AR} | $I_D=8\text{ A}, V_{DD}=50\text{ V}$ | 0.2 | |
| Avalanche current, repetitive t_{AR} ^{3),4)} | I_{AR} | | 8 | A |
| MOSFET dv/dt ruggedness | dv/dt | $V_{DS}=0\dots640\text{ V}$ | 50 | V/ns |
| Gate source voltage | V_{GS} | static | ± 20 | V |
| | | AC ($f>1\text{ Hz}$) | ± 30 | |
| Power dissipation | P_{tot} | $T_C=25^\circ\text{C}$ | 40 | W |
| Operating and storage temperature | T_j, T_{stg} | | -55 ... 150 | $^\circ\text{C}$ |
| Mounting torque | | M2.5 screws | 50 | Ncm |

Maximum ratings, at $T_j=25\text{ °C}$, unless otherwise specified

| Parameter | Symbol | Conditions | Value | Unit |
|-------------------------------------|---------------|--------------------|-------|------|
| Continuous diode forward current | I_S | $T_C=25\text{ °C}$ | 8 | A |
| Diode pulse current ²⁾ | $I_{S,pulse}$ | | 24 | |
| Reverse diode dv/dt ⁴⁾ | dv/dt | | 4 | V/ns |

| Parameter | Symbol | Conditions | Values | | | Unit |
|-----------|--------|------------|--------|------|------|------|
| | | | min. | typ. | max. | |

Thermal characteristics

| | | | | | | |
|---|------------|--------------------------------------|---|---|-----|-----|
| Thermal resistance, junction - case | R_{thJC} | | - | - | 3.8 | K/W |
| Thermal resistance, junction - ambient | R_{thJA} | leaded | - | - | 80 | |
| Soldering temperature, wave soldering only allowed at leads | T_{sold} | 1.6 mm (0.063 in.) from case for 10s | - | - | 260 | °C |

Electrical characteristics, at $T_j=25\text{ °C}$, unless otherwise specified
Static characteristics

| | | | | | | |
|----------------------------------|---------------|---|-----|------|------|---------------|
| Drain-source breakdown voltage | $V_{(BR)DSS}$ | $V_{GS}=0\text{ V}$, $I_D=250\text{ }\mu\text{A}$ | 800 | - | - | V |
| Avalanche breakdown voltage | $V_{(BR)DS}$ | $V_{GS}=0\text{ V}$, $I_D=8\text{ A}$ | - | 870 | - | |
| Gate threshold voltage | $V_{GS(th)}$ | $V_{DS}=V_{GS}$, $I_D=0.47\text{ mA}$ | 2.1 | 3 | 3.9 | |
| Zero gate voltage drain current | I_{DSS} | $V_{DS}=800\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=25\text{ °C}$ | - | - | 20 | μA |
| | | $V_{DS}=800\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=150\text{ °C}$ | - | 100 | - | |
| Gate-source leakage current | I_{GSS} | $V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$ | - | - | 100 | nA |
| Drain-source on-state resistance | $R_{DS(on)}$ | $V_{GS}=10\text{ V}$, $I_D=5.1\text{ A}$, $T_j=25\text{ °C}$ | - | 0.56 | 0.65 | Ω |
| | | $V_{GS}=10\text{ V}$, $I_D=5.1\text{ A}$, $T_j=150\text{ °C}$ | - | 1.5 | - | |
| Gate resistance | R_G | $f=1\text{ MHz}$, open drain | - | 1.2 | - | Ω |

| Parameter | Symbol | Conditions | Values | | | Unit |
|-----------|--------|------------|--------|------|------|------|
| | | | min. | typ. | max. | |

Dynamic characteristics

| | | | | | | |
|--|--------------|---|---|------|---|----|
| Input capacitance | C_{iss} | $V_{GS}=0\text{ V}, V_{DS}=100\text{ V},$ $f=1\text{ MHz}$ | - | 1100 | - | pF |
| Output capacitance | C_{oss} | | - | 46 | - | |
| Effective output capacitance, energy related ⁵⁾ | $C_{o(er)}$ | $V_{GS}=0\text{ V}, V_{DS}=0\text{ V}$ to 480 V | - | 36 | - | |
| Effective output capacitance, time related ⁶⁾ | $C_{o(tr)}$ | | - | 99 | - | |
| Turn-on delay time | $t_{d(on)}$ | $V_{DD}=400\text{ V},$ $V_{GS}=0/10\text{ V}, I_D=8\text{ A},$ $R_G=10\ \Omega, T_j=25\text{ }^\circ\text{C}$ | - | 25 | - | ns |
| Rise time | t_r | | - | 15 | - | |
| Turn-off delay time | $t_{d(off)}$ | | - | 72 | - | |
| Fall time | t_f | | - | 10 | - | |

Gate Charge Characteristics

| | | | | | | |
|-----------------------|---------------|--|---|-----|----|----|
| Gate to source charge | Q_{gs} | $V_{DD}=640\text{ V}, I_D=8\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$ | - | 6 | - | nC |
| Gate to drain charge | Q_{gd} | | - | 22 | - | |
| Gate charge total | Q_g | | - | 45 | 60 | |
| Gate plateau voltage | $V_{plateau}$ | | - | 5.5 | - | V |

Reverse Diode

| | | | | | | |
|-------------------------------|-----------|---|---|-----|-----|---------------|
| Diode forward voltage | V_{SD} | $V_{GS}=0\text{ V}, I_F=I_S=8\text{ A},$ $T_j=25\text{ }^\circ\text{C}$ | - | 1 | 1.2 | V |
| Reverse recovery time | t_{rr} | $V_R=400\text{ V}, I_F=I_S=8\text{ A},$ $di_F/dt=100\text{ A}/\mu\text{s}$ | - | 550 | - | ns |
| Reverse recovery charge | Q_{rr} | | - | 7 | - | μC |
| Peak reverse recovery current | I_{rrm} | | - | 24 | - | A |

¹⁾ J-STD20 and JESD22

²⁾ Pulse width t_p limited by $T_{j,max}$

³⁾ Repetitive avalanche causes additional power losses that can be calculated as $P_{AV}=E_{AR} \cdot f$.

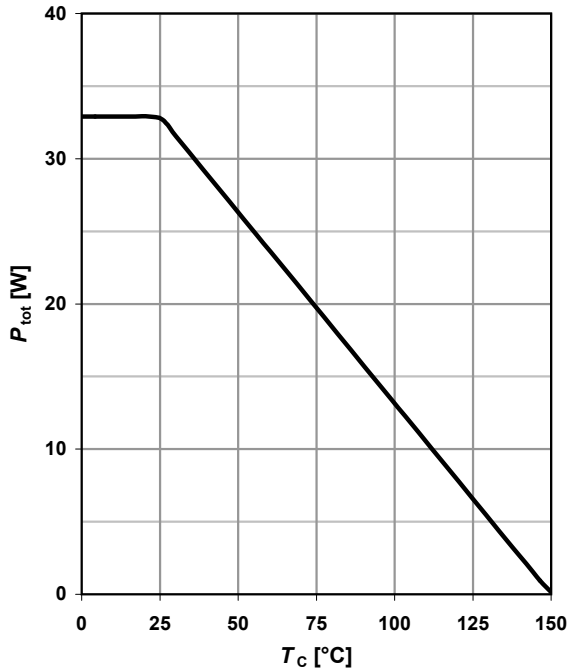
⁴⁾ $I_{SD} \leq I_D$, $di/dt \leq 400\text{ A}/\mu\text{s}$, $V_{DClink} = 400\text{ V}$, $V_{peak} < V_{(BR)DSS}$, $T_j < T_{j,max}$, identical low side and high side switch

⁵⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

⁶⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

1 Power dissipation

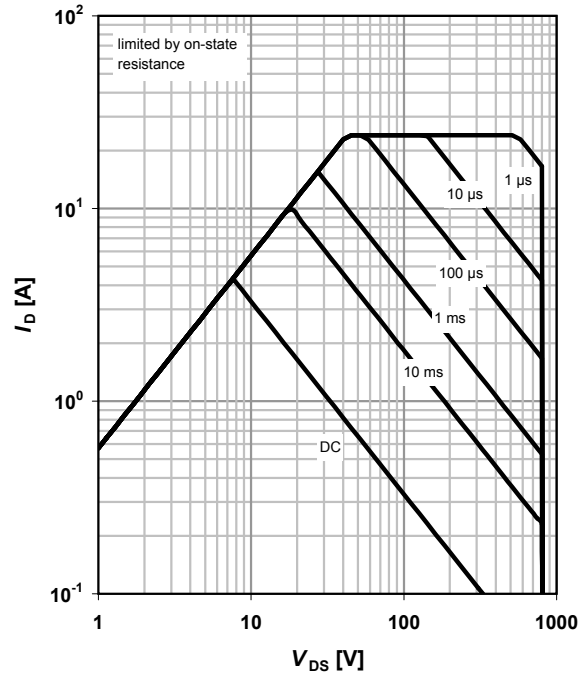
$P_{tot}=f(T_C)$



2 Safe operating area

$I_D=f(V_{DS}); T_C=25\text{ °C}; D=0$

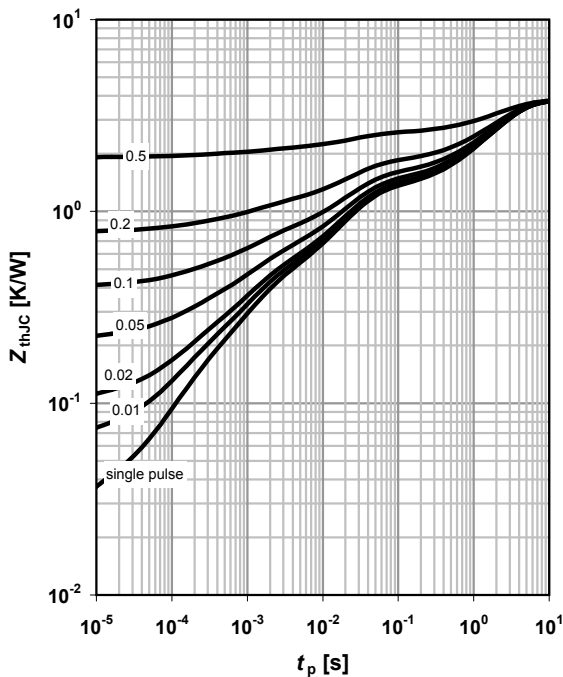
parameter: t_p



3 Max. transient thermal impedance

$Z_{thJC}=f(t_p)$

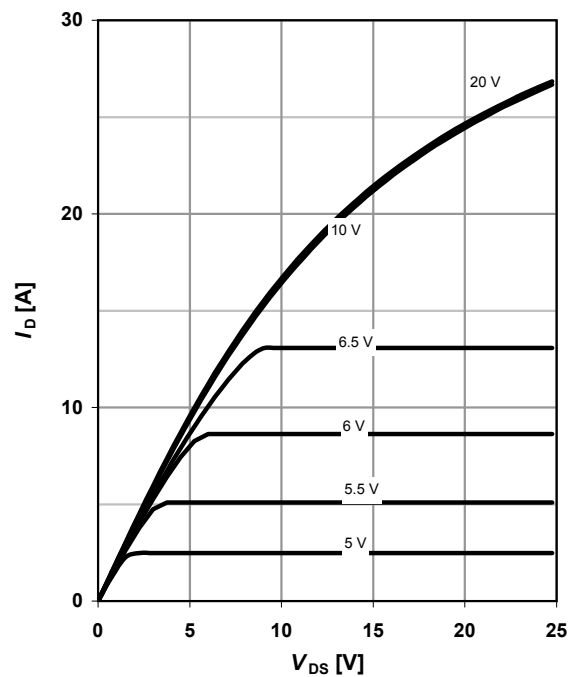
parameter: $D=t_p/T$



4 Typ. output characteristics

$I_D=f(V_{DS}); T_J=25\text{ °C}; t_p=10\text{ µs}$

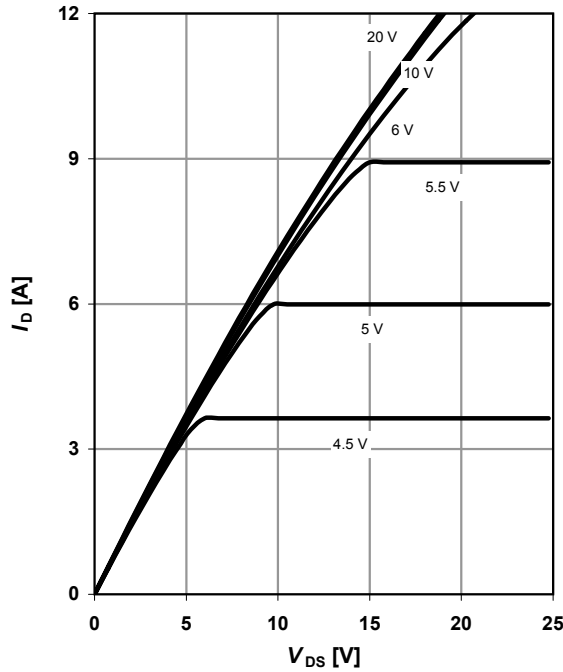
parameter: V_{GS}



5 Typ. output characteristics

$I_D = f(V_{DS}); T_j = 150\text{ °C}; t_p = 10\text{ }\mu\text{s}$

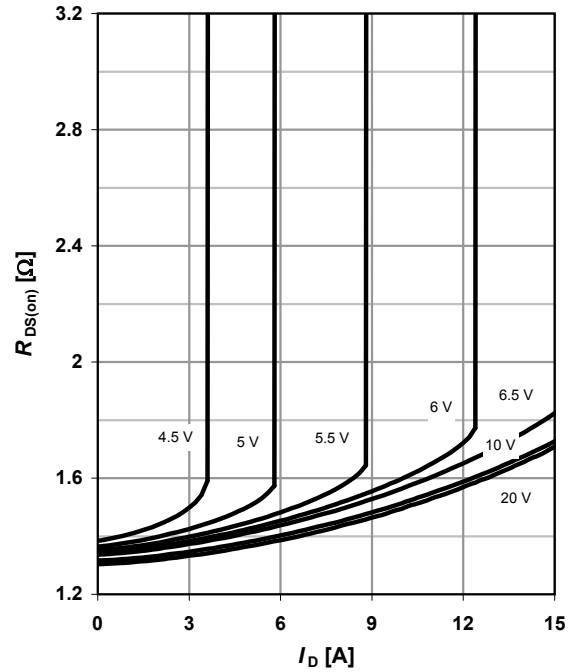
parameter: V_{GS}



6 Typ. drain-source on-state resistance

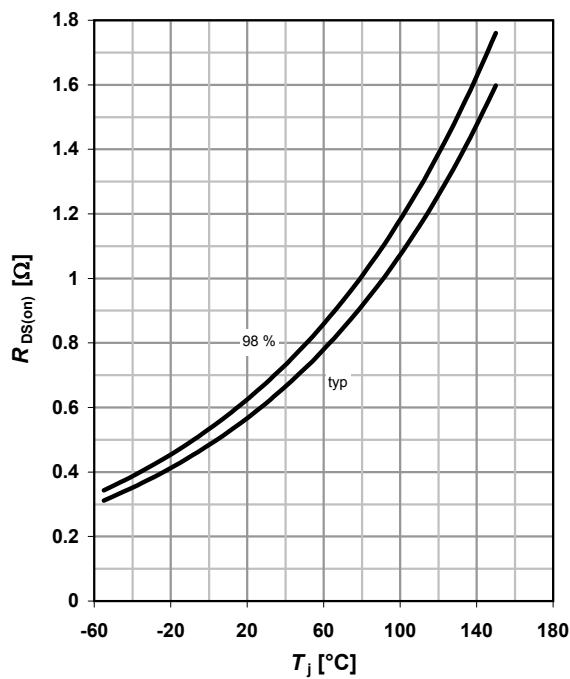
$R_{DS(on)} = f(I_D); T_j = 150\text{ °C}$

parameter: V_{GS}



7 Drain-source on-state resistance

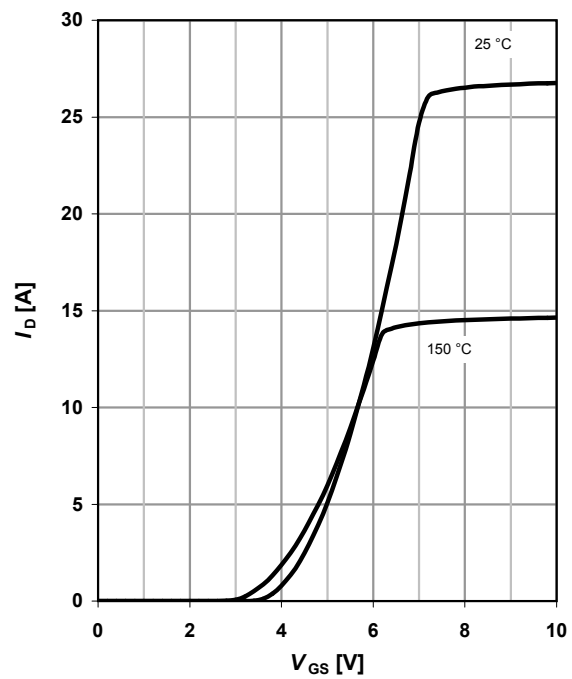
$R_{DS(on)} = f(T_j); I_D = 5.1\text{ A}; V_{GS} = 10\text{ V}$



8 Typ. transfer characteristics

$I_D = f(V_{GS}); |V_{DS}| > 2I_D/R_{DS(on)max}; t_p = 10\text{ }\mu\text{s}$

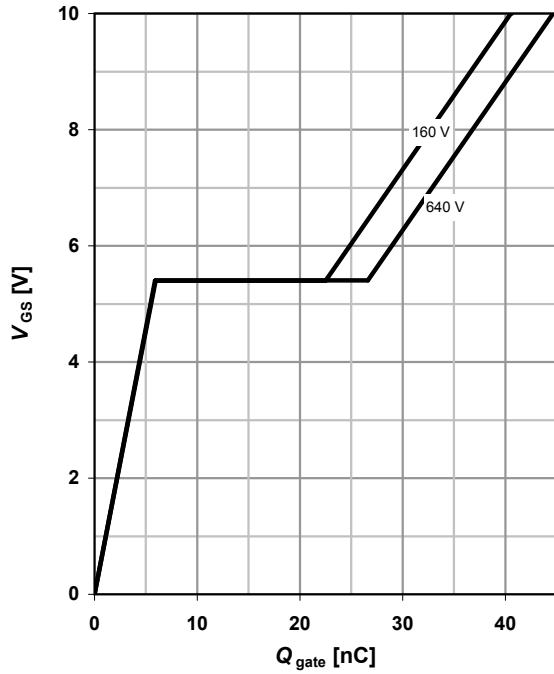
parameter: T_j



9 Typ. gate charge

$V_{GS}=f(Q_{gate}); I_D=8\text{ A pulsed}$

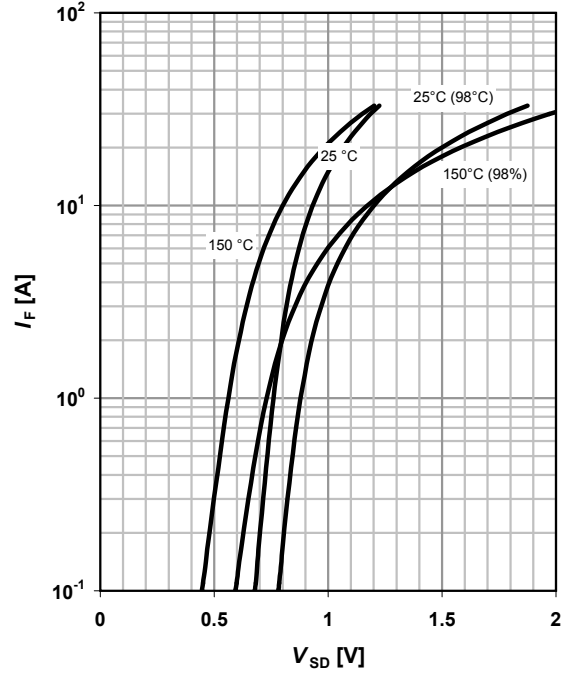
parameter: V_{DD}



10 Forward characteristics of reverse diode

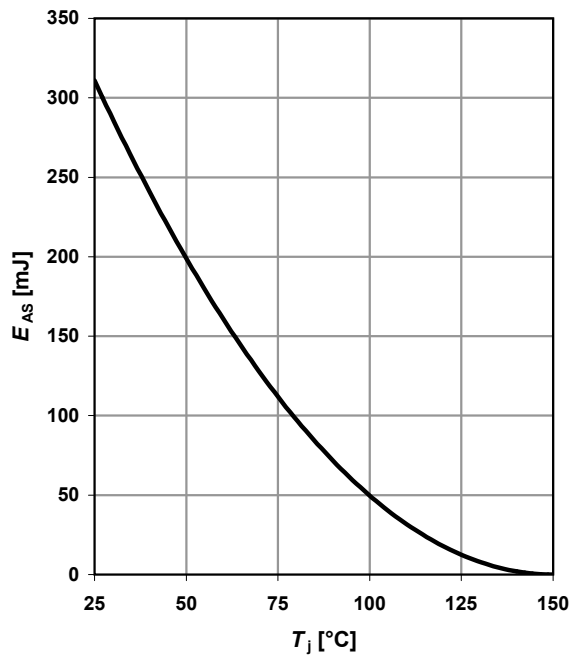
$I_F=f(V_{SD}); t_p=10\ \mu\text{s}$

parameter: T_j



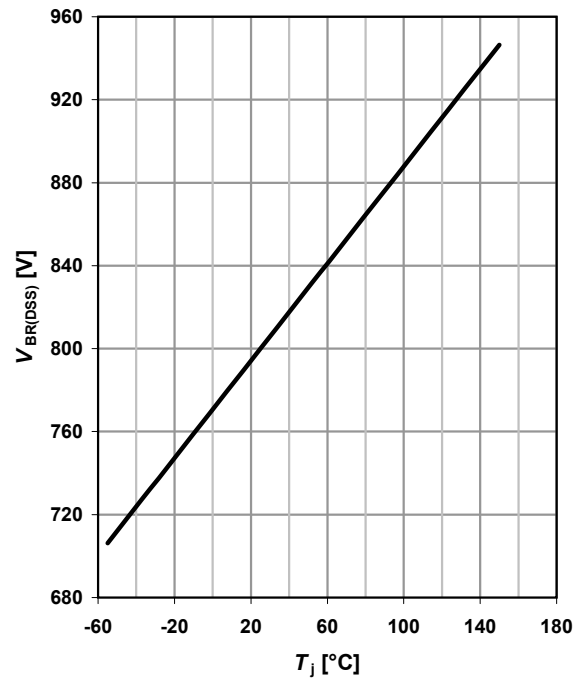
11 Avalanche energy

$E_{AS}=f(T_j); I_D=1.6\text{ A}; V_{DD}=50\text{ V}$



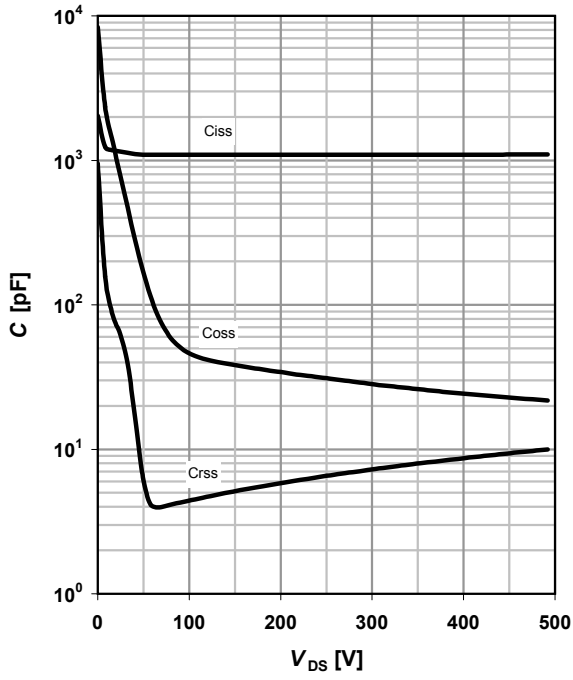
12 Drain-source breakdown voltage

$V_{BR(DSS)}=f(T_j); I_D=0.25\text{ mA}$



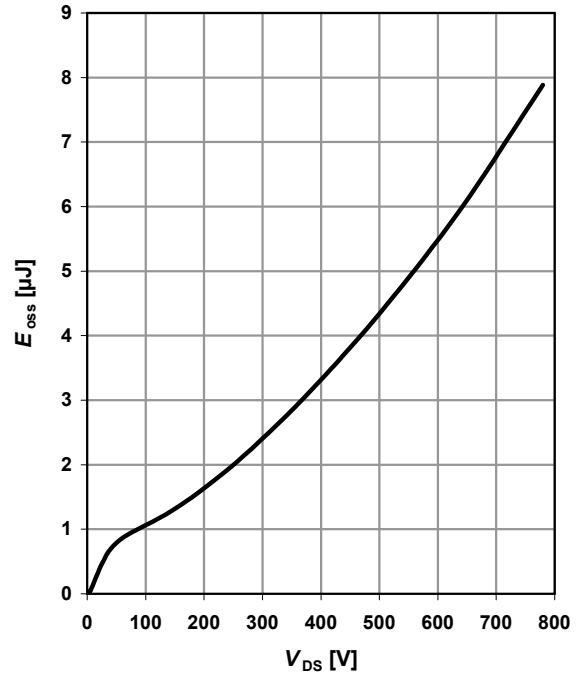
13 Typ. capacitances

$C=f(V_{DS}); V_{GS}=0\text{ V}; f=1\text{ MHz}$



14 Typ. Coss stored energy

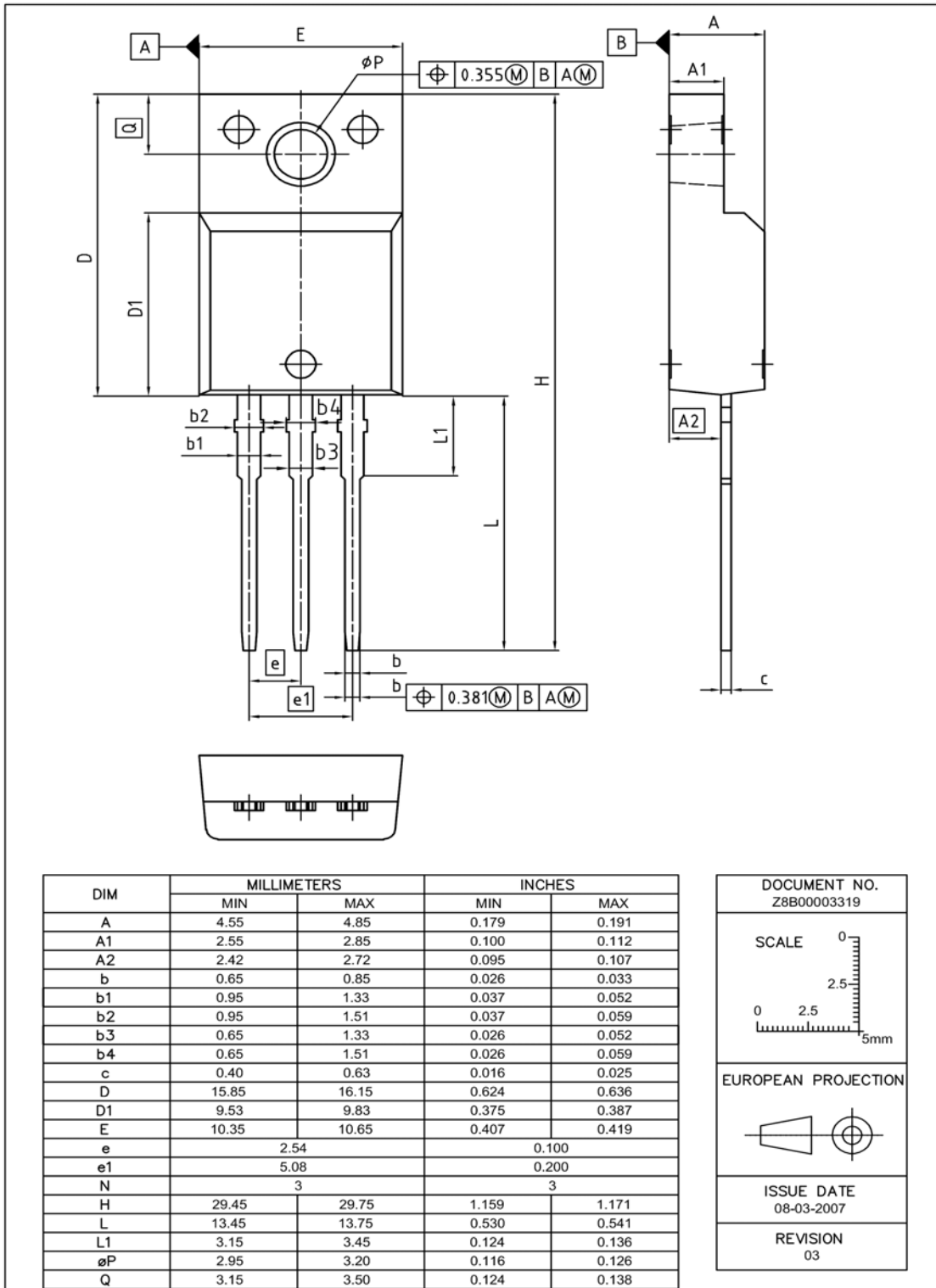
$E_{oss}=f(V_{DS})$



Definition of diode switching characteristics



PG-TO220-3 (Fully isolated)



Dimensions in mm/ inches

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